

## THE UNITED STATES PATENT AND TRADEMARK OFFICE

**REVOCATION AND NEW POWER OF ATTORNEY AND  
CHANGE OF CORRESPONDENCE ADDRESS**

I, *Dr. Graham Fisher, Director of Intellectual Property of MEMC Electronic Materials, Inc.*, the Assignee of the entire right, title, and interest in the *U.S. Patent Application(s) and/or Patent(s) identified on the attached Schedule A*, hereby revoke all previous powers of attorney or authorizations of agent given and do hereby appoint the attorneys or agents associated with the following Customer Number, with full power of substitution and revocation, to prosecute and transact all business in the Patent and Trademark Office connected therewith for the *U.S. Patent Application(s) and/or Patent(s) listed in the attached Schedule A*:

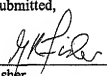
*Customer Number: 76681*

Please direct all correspondence in connection with said *U.S. Patent Application(s) and/or Patent(s)* to:

*Customer Number: 76681*

Respectfully submitted,

Date: 5/13/2008

  
\_\_\_\_\_  
Dr. Graham Fisher  
Director of Intellectual Property  
MEMC Electronic Materials, Inc.

PATENT

THE UNITED STATES PATENT AND TRADEMARK OFFICE

**STATEMENT UNDER 37 CFR 3.73(b)**


***MEMC Electronic Materials, Inc.***, a Delaware Corporation, pursuant to 37 CFR 3.73(b), hereby states that it is the Assignee of the entire right, title, and interest in ***U.S. Patent Application(s) and/or Patent(s) on the attached Schedule A.***

The entire rights, title, and interest in the aforementioned Patent Application(s) and/or Patent(s) were conveyed to ***MEMC Electronic Materials, Inc.*** via Assignment(s) recorded with the United States Patent and Trademark Office at the ***Reel/Frame Numbers on the attached Schedule A.***

The undersigned, ***Dr. Graham Fisher, Director of Intellectual Property***, has full authorization to act on behalf of Assignee ***MEMC Electronic Materials, Inc.***

Respectfully submitted,

Date: 5/13/2008

  
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Dr. Graham Fisher  
Director of Intellectual Property  
MEMC Electronic Materials, Inc.

**APPENDIX A**  
**Owned by MEMC Electronic Materials, Inc.**

ATTORNEY REFERENCE	CONF. NO.	PUBLICATION NO. & DATE	SERIAL NO. FILING DATE	PATENT NO. ISSUE DATE	CURRENT OWNER/ ASSIGNEE	REEL AND FRAME NO.	TITLE
MEMC2495.1	9140	US-2002-0200105-A1 1/3/2002	09/020,565 9/14/2001	6,432,187 6/13/2002	MEMC Electronic Materials, Inc.	Continuation of 09/079,353 recorded at 01/12/96/0888	PROCESS FOR THE PREPARATION OF NON-OXYGEN PRECIPITATING CZOCHELSKI SILICON WAFERS
MEMC2495.2	1234	US-2002-0189528-A1 12/19/2002	01/217,703 9/13/2002	6,705,611 3/23/2004	MEMC Electronic Materials, Inc.	Continuation of 09/029,535 recorded at 01/12/96/0888	PROCESS FOR SUPPRESSING OXYGEN PRECIPITATION IN VACUUM DOMINATED SILICON
MEMC2499	8355		09/404,428 9/28/1999	6,214,704 4/10/2001	MEMC Electronic Materials, Inc.	01/039,900/180	METHOD OF PROCESSING SEMICONDUCTOR WAFERS TO BUILD IN BACK SURFACE DAMAGE
MEMC2503	8725		09/345,103 9/27/1999	6,361,619 3/29/2002	MEMC Electronic Materials, Inc.	01/039,900/004	THERMALLY ANNEALED WAFERS HAVING IMPROVED INTERNAL GETTERING
MEMC2503.1	8207	US-2002-0170631-A1 11/2/2002	10/037,070 2/4/2002	6,696,260 2/3/2004	MEMC Electronic Materials, Inc.	Division of 09/385,104 recorded at 01/03/00/0004	PROCESS FOR PRODUCING THERMALLY ANNEALED WAFERS HAVING IMPROVED INTERNAL GETTERING
MEMC2507	8140		09/384,688 9/27/1999	6,191,010 2/20/2001	MEMC Electronic Materials, Inc.	01/072,405/25	PROCESS FOR PREPARING AN IDEAL OXYGEN PRECIPITATING SILICON WAFER
MEMC2512	2402		09/387,288 9/31/1999	6,236,104 5/22/2001	MEMC Electronic Materials, Inc.	01/044,909/40	SILICON ON INSULATOR STRUCTURE FROM LOW DEFECT DENSITY SINGLE CRYSTAL SILICON
MEMC2512.1	9249	US-2001-0030348-A1 10/18/2001	09/737,715 12/15/2000	6,342,725 1/29/2002	MEMC Electronic Materials, Inc.	Continuation of 09/387,288 recorded at 01/04/98/0840	SILICON ON INSULATOR STRUCTURE HAVING A LOW DEFECT DENSITY HANDLE WAFER AND PROCESS FOR THE PREPARATION THEREOF
MEMC2512.2	7383	US-2002-0113285-A1 8/22/2002	10/039,084 1/3/2002	6,849,901 2/1/2005	MEMC Electronic Materials, Inc.	Division of 09/737,715 which is a continuation of 09/387,288 recorded at 01/04/98/0840	A SILICON-ON-INSULATOR STRUCTURE HAVING A DEVICE LAYER WHICH IS VACUUM DOMINATED AND SUBSTANTIALLY FREE OF AGGLOMERATED VACUANCY-TYPE DEFECTS
MEMC2516	1795		09/432,928 11/3/1999	6,259,139 9/25/2001	MEMC Electronic Materials, Inc.	01/045,901/180	METHOD OF DETERMINING PERFORMANCE CHARACTERISTICS OF POLISHING PAD
MEMC2524	2877		09/507,811 2/22/2000	6,514,423 2/4/2003	MEMC Electronic Materials, Inc.	01/062,702/92	METHOD FOR WAFER PROCESSING
MEMC2553	7647		09/417,610 10/13/1999	6,284,039 9/4/2001	MEMC Electronic Materials, Inc.	01/049,405/49	EPITAXIAL SILICON WAFERS SUBSTANTIALLY FREE OF GROWN-IN DEFECTS
MEMC2553.1	8168	US-2001-003916-A1 11/19/2001	09/874,487 9/6/2001	6,566,549 5/20/2003	MEMC Electronic Materials, Inc.	Continuation of 09/417,610 recorded at 01/04/98/0840	AN EPITAXIAL WAFER SUBSTANTIALLY FREE OF GROWN-IN DEFECTS
MEMC2553.2	3406	US-2003-020519-A1 11/6/2003	10/441,413 5/20/2003	7,097,718 8/29/2006	MEMC Electronic Materials, Inc.	Continuation of 09/874,487 which is a continuation of 09/417,610 recorded at 01/04/98/0840	SINGLE CRYSTAL SILICON WAFER HAVING AN EPITAXIAL LAYER SUBSTANTIALLY FREE FROM GROWN-IN DEFECTS